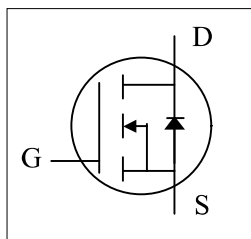


# AP2080KA

## N-Channel Power MOSFET

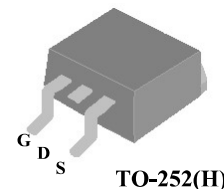
- ▼ Capable of 2.5V Gate Drive
- ▼ Small Size & Ultra\_Low  $R_{DS(ON)}$
- ▼ RoHS Compliant & Halogen-Free



$BV_{DSS}$	20V
$R_{DS(ON)}$	8.8m $\Omega$
$I_D^3$	50A

### Description

AP2080KA series are from Advanced Power innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.



### Absolute Maximum Ratings@ $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	20	V
$V_{GS}$	Gate-Source Voltage	$\pm 12$	V
$I_D@T_A=25^\circ\text{C}$	Drain Current, $V_{GS} @ 4.5\text{V}^3$	50	A
$I_D@T_A=70^\circ\text{C}$	Drain Current, $V_{GS} @ 4.5\text{V}^3$	45	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	90	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation	3.13	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

### Thermal Data

Symbol	Parameter	Value	Unit
Rthj-c	Maximum Thermal Resistance, Junction-case	5	$^\circ\text{C}/\text{W}$
Rthj-a	Maximum Thermal Resistance, Junction-ambient <sup>3</sup>	40	$^\circ\text{C}/\text{W}$

**AP2080KA**
**N-Channel Power MOSFET**
**Electrical Characteristics@T<sub>j</sub>=25°C(unless otherwise specified)**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	20	-	-	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A	-	8.8	9.8	mΩ
		V <sub>GS</sub> =2.5V, I <sub>F</sub> =12A	-	-	14	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =1mA	0.6	-	0.9	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =20A	-	130	-	S
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =16V, V <sub>GS</sub> =0V	-	-	10	uA
I <sub>GSS</sub>	Gate-Source Leakage	V <sub>GS</sub> =±12V, V <sub>DS</sub> =0V	-	-	±100	nA
Q <sub>g</sub>	Total Gate Charge	I <sub>D</sub> =20A	-	31	62.2	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =10V	-	2	-	nC
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	V <sub>GS</sub> =4.5V	-	11	-	nC
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DS</sub> =10V	-	6	-	ns
t <sub>r</sub>	Rise Time	I <sub>D</sub> =1A	-	10	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time	R <sub>G</sub> =3.3Ω	-	50	-	ns
t <sub>f</sub>	Fall Time	V <sub>GS</sub> =5V	-	40	-	ns
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V	-	1100	2200	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =10V	-	390	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1.0MHz	-	312	-	pF
R <sub>g</sub>	Gate Resistance	f=1.0MHz	-	1.4	2.8	Ω

**Source-Drain Diode**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V <sub>SD</sub>	Forward On Voltage <sup>2</sup>	I <sub>S</sub> =2.5A, V <sub>GS</sub> =0V	-	-	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>S</sub> =20A, V <sub>GS</sub> =0V,	-	21	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	di/dt=100A/μs	-	26	-	nC

**Notes:**

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Surface mounted on 1 in<sup>2</sup> 2oz copper pad of FR4 board, t ≤10sec; 135°C/W when mounted on min. copper pad.
- 4.Maximum current limited by package.

Typical Electrical and Thermal Characteristics (Curves)

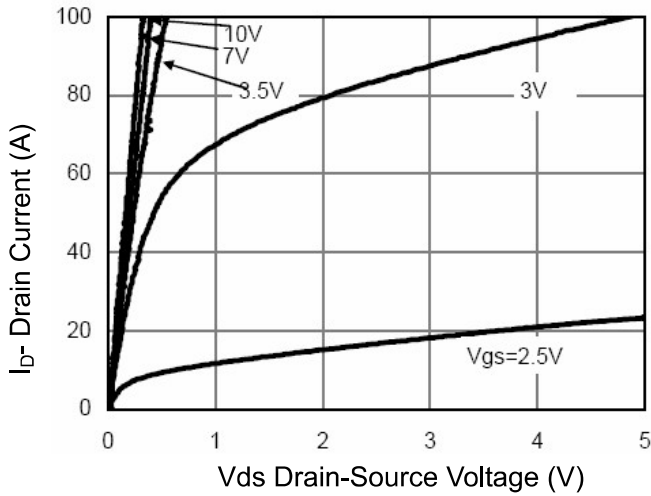


Figure 1 Output Characteristics

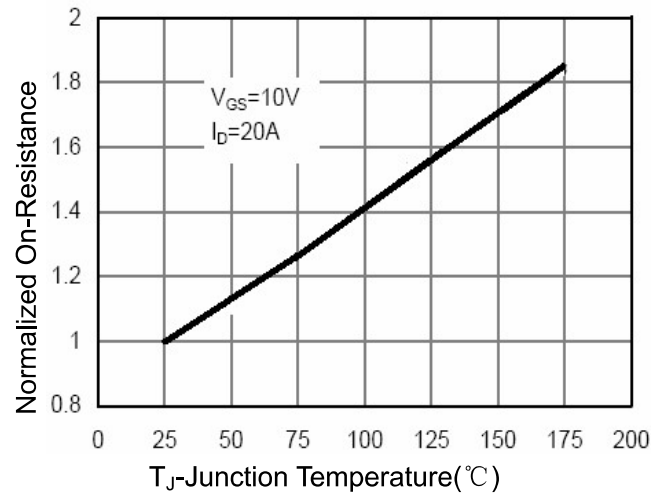


Figure 4 Rdson-Junction Temperature

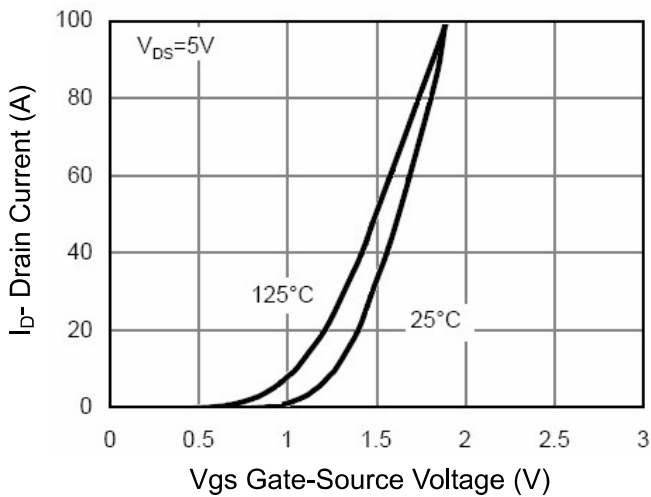


Figure 2 Transfer Characteristics

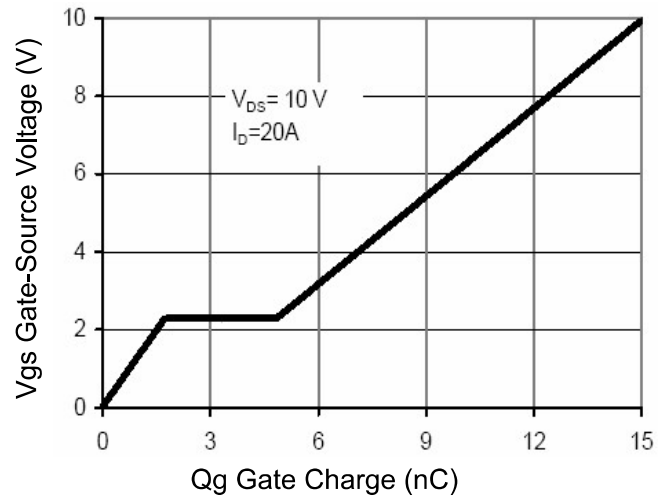


Figure 5 Gate Charge

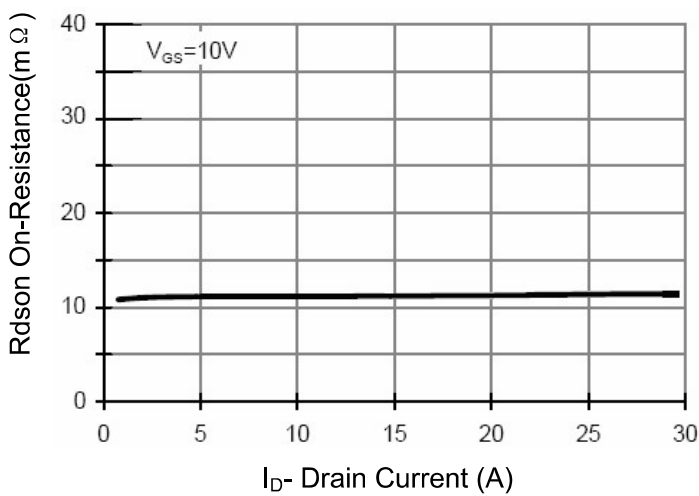


Figure 3 Rdson- Drain Current

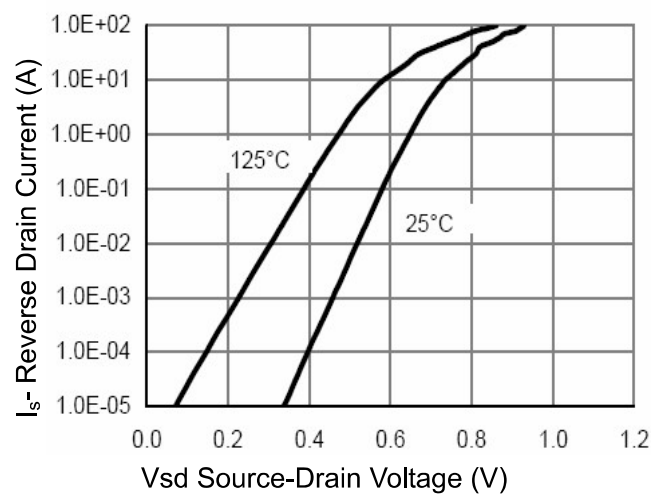
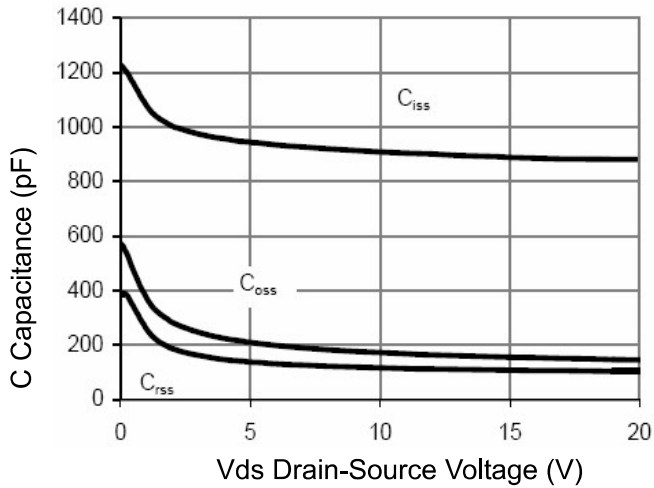


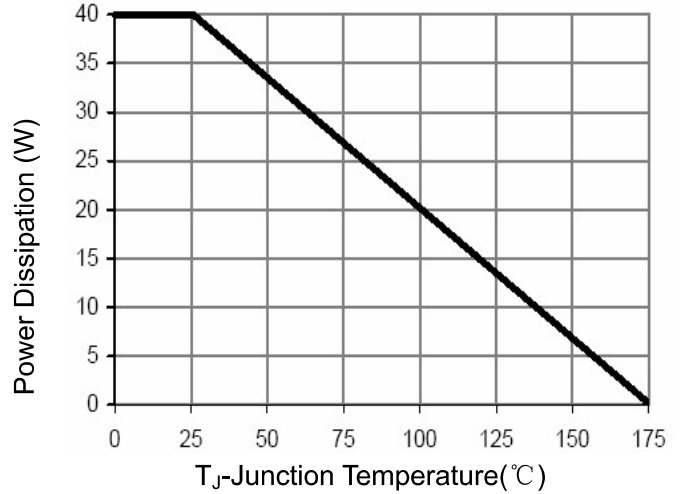
Figure 6 Source- Drain Diode Forward

**AP2080KA**

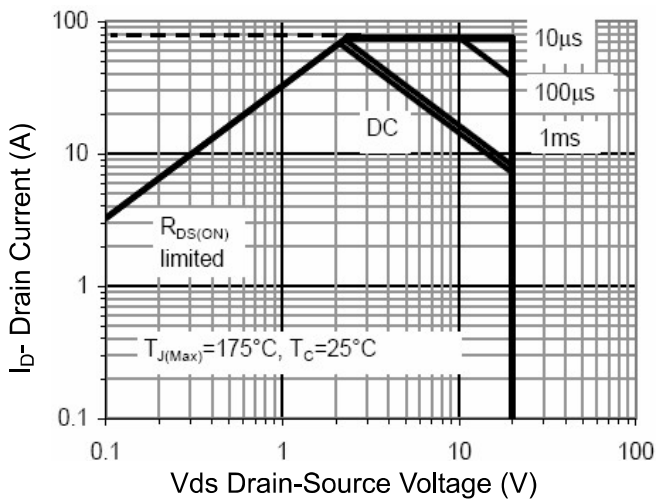
**N-Channel Power MOSFET**



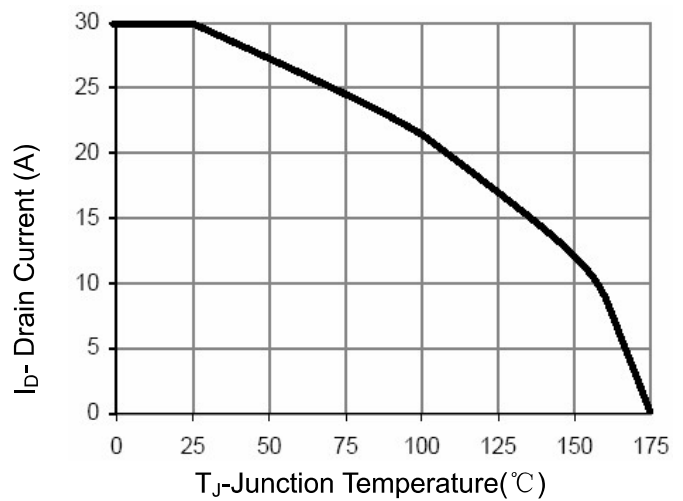
**Figure 7 Capacitance vs Vds**



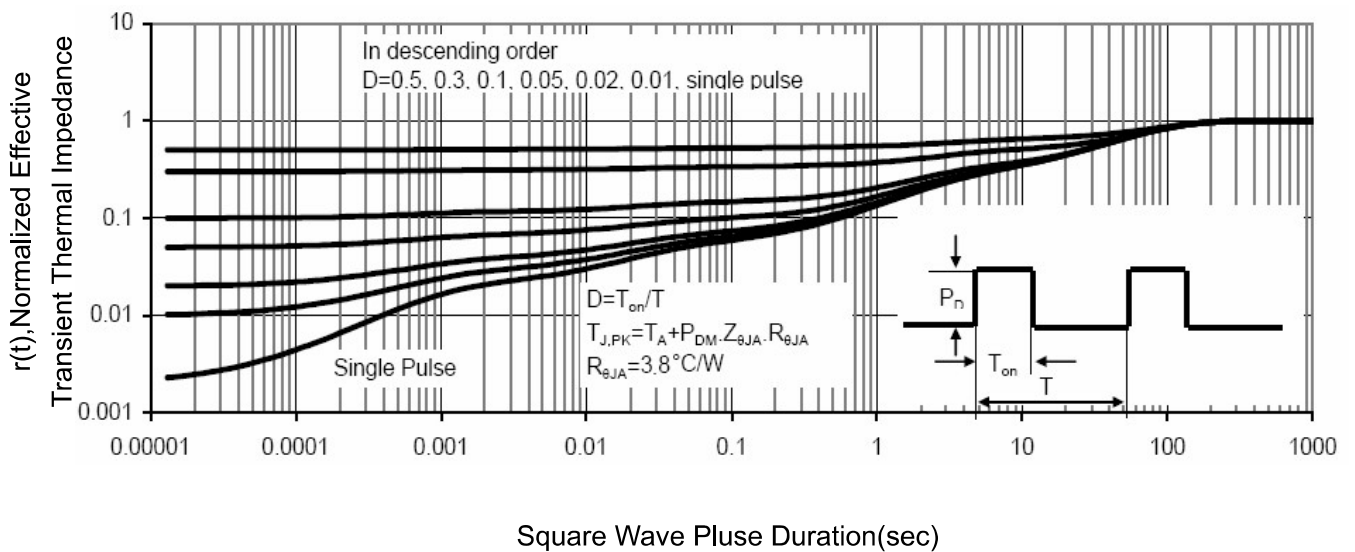
**Figure 9 Power De-rating**



**Figure 8 Safe Operation Area**



**Figure 10 Current De-rating**



**Figure 11 Normalized Maximum Transient Thermal Impedance**

**AP2080KA**  
**N-Channel Power MOSFET**

**MARKING INFORMATION**

TO-252

